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## 师资力量

院士介绍

人员构成

## 安霞



职称：副教授

研究所：微纳电子学研究院

研究领域：新型微纳器件及其相关集成技术研究；新型微纳器件辐射效应、损伤机理及加固技术研究

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### 科研/教育经历

2006年1月北京大学微电子学与固体电子学博士毕业，获理学博士学位。毕业后留校工作，2010年8月起任职副教授。

### 主要研究方向

现主要从事新型微纳器件及其相关集成技术研究；新型微纳器件辐射效应、损伤机理及加固技术研究方面的工作。

### 研究成果概况

主持国家科技重大专项1项（“新结构器件研究”）、国家自然科学基金（青年基金）项目、预研项目各1项，作为课题负责人参加973项目2项；作为北大方负责人参加国家自然科学基金重点项目2项，作为技术骨干参加973课题1项、国家科技重大专项2项。《半导体学报》编委，是《IEEE Transactions on Electron Devices》、《IEEE Transactions on Nuclear Science》、《Journal of Applied Physics》、《中国科学》、《物理学报》、《半导体学报》、《中国物理快报》等期刊审稿人。在EDL、APL、SST等国内外学术期刊发表论文40余篇，申请国内发明专利50余项、国际发明专利10项。

### 代表性学术论著

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